

# K4N25G • K4N25H

These Photocouplers consist of a Gallium Arsenide Infrared Emitting Diode and a Silicon NPN Phototransistor in a 6-pin package.

## FEATURES

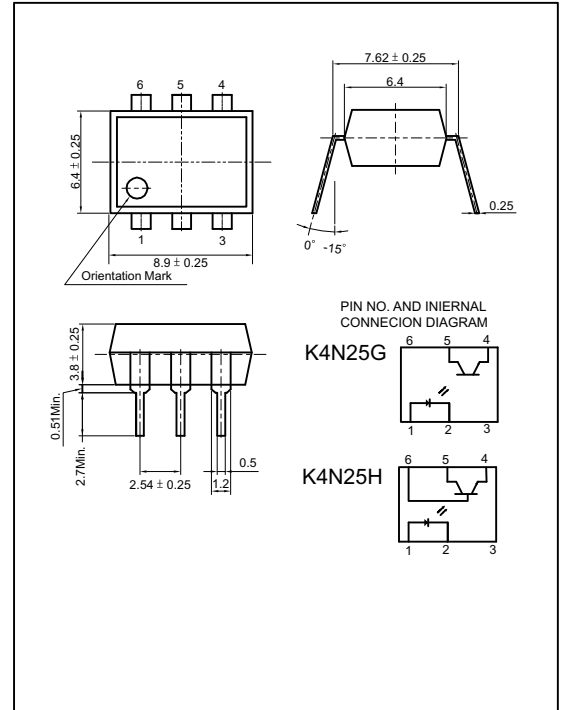
- TTL Compatible Output
- Collector-Emitter Voltage : Min.50V
- Current Transfer Ratio : Typ.100% (at IF=5mA, VCE=5V)
- Electrical Isolation Voltage : AC5000Vrms
- UL Recognized File No. E107486
- K4N25G - No Base Connection,  
K4N25H - With Base Connection

## APPLICATIONS

- Interface between two circuits of different potential
- Vending Machine, Copiers
- Measuring Instrument
- Home Appliances

## DIMENSION

(Unit : mm)



## MAXIMUM RATINGS

(Ta=25 )

Parameter		Symbol	Rating	Unit
Input	Forward Current	IF	50	mA
	Reverse Voltage	VR	5	V
	Peak Forward Current <sup>*1</sup>	IFP	1	A
	Power Dissipation	PD	70	mW
Output	Collector-Emitter Breakdown Voltage	BVCEO	50	V
	Emitter-Collector Breakdown Voltage	BVECO	6	V
	Collector-Base Breakdown Voltage**	BVCBO	80	V
	Emitter-Base Breakdown Voltage**	BVEBO	6	V
	Collector Current	IC	50	mA
	Collector Power Dissipation	PC	150	mW
Input to Output Isolation Voltage <sup>*2</sup>		Viso	AC5000	Vrms
Storage Temperature		Tstg	-55~+125	
Operating Temperature		Topr	-30~+100	
Lead Soldering Temperature <sup>*3</sup>		Tsol	260	
Total Power Dissipation		Ptot	200	mW

\*\* Except for K4N25G

\*1. Input current with 100μs pulse width, 1% duty cycle

\*2. Measured at RH=40~60% for 1min

\*3. 1/16 inch form case for 10sec

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### ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25 , unless otherwise noted)

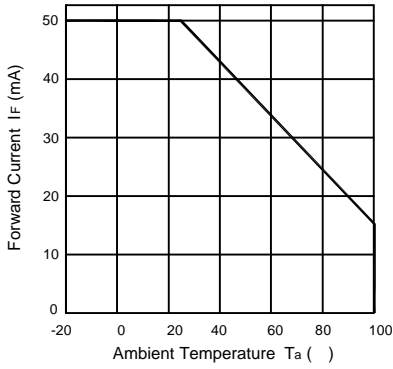
Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit.
Input	Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =10mA	-	1.15	1.30	V
	Reverse Current	I <sub>R</sub>	V <sub>R</sub> =5V	-	-	10	mA
	Capacitance	C <sub>T</sub>	V=0, f=1MHz	-	30	-	pF
Output	Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =0.5mA	50	-	-	V
	Emitter-Collector Breakdown Voltage	BV <sub>ECO</sub>	I <sub>E</sub> =0.1mA	6	-	-	V
	Collector-Base Breakdown Voltage **	BV <sub>CBO</sub>	I <sub>C</sub> =0.1mA	80	-	-	V
	Emitter-Base Breakdown Voltage **	BV <sub>EBO</sub>	I <sub>E</sub> =0.1mA	6	-	-	V
	Collector Dark Current	I <sub>CEO</sub>	I <sub>F</sub> =0, V <sub>CE</sub> =10V	-	-	100	nA
	Capacitance	C <sub>CE</sub>	V <sub>CE</sub> =0, f=1MHz	-	10	-	pF
Coupled	Current Transfer Ratio *4	CTR	I <sub>F</sub> =5mA, V <sub>CE</sub> =5V	50	-	600	%
	Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>F</sub> =5mA, I <sub>C</sub> =1mA	-	-	0.4	V
	Input-Output Capacitance	C <sub>IO</sub>	V=0, f=1MHz	-	1	-	pF
	Input-Output Isolation Resistance	R <sub>IO</sub>	RH=40~60%, V=500V	-	10 <sup>11</sup>	-	
	Rise Time	t <sub>r</sub>	V <sub>CC</sub> =10V, R <sub>L</sub> =100	-	3	-	μs
	Fall Time	t <sub>f</sub>	I <sub>C</sub> =2mA	-	3	-	μs

\*\* Except for K4N25G

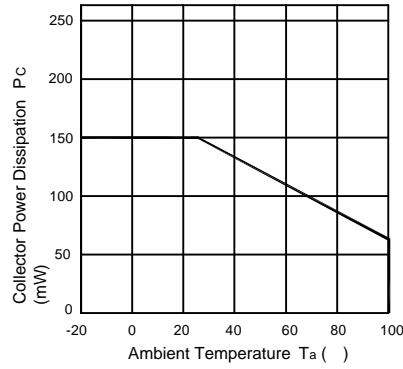
\*4. CTR=(I<sub>C</sub>/I<sub>F</sub>) X 100 (%)

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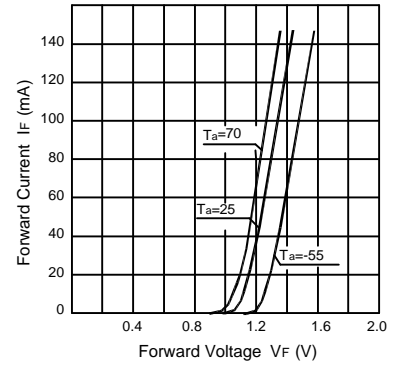
**Forward Current vs. Ambient Temperature**



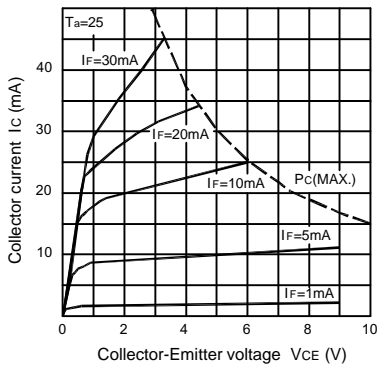
**Collector Power Dissipation vs. Ambient Temperature**



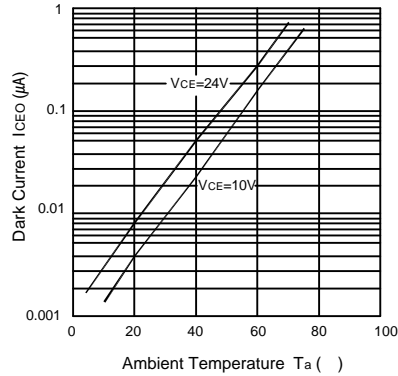
**Forward Current vs. Forward Voltage**



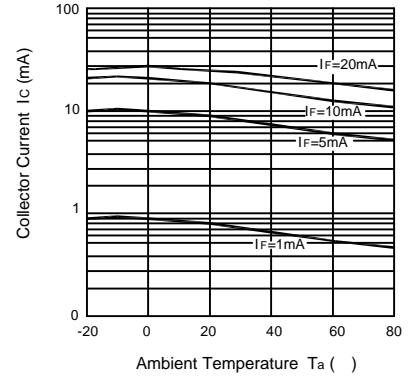
**Collector Current vs. Collector-Emitter Voltage**



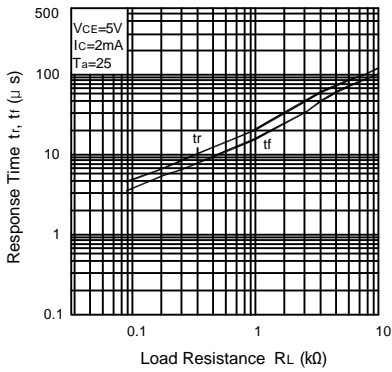
**Dark Current vs. Ambient Temperature**



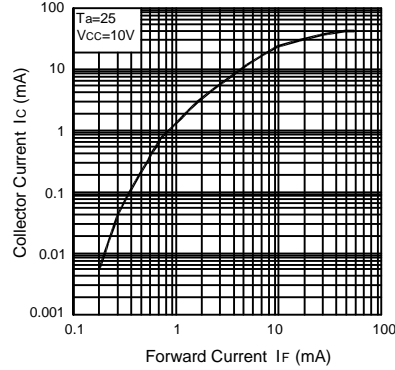
**Collector Current vs. Ambient Temperature**



**Response Time vs. Load Resistance**



**Collector Current vs. Forward Current**



**Switching Time Test Circuit**

